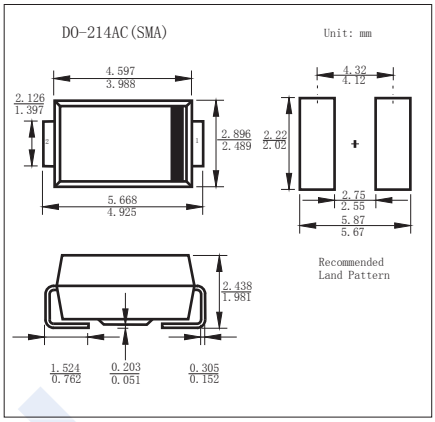
Schottky Diodes

SB220 ~ SB2200



■ Features

- Metal silicon junction,majority carrier conduction
- Low power loss,high efficiency
- High forward surge current capability

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	SB 220	SB 230	SB 240	SB 250	SB 260	SB 270	SB 280	SB 290	SB 2100	SB 2150	SB 2200	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}	20	30	40	50	60	70	80	90	100	150	200	V
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	35	42	49	56	63	70	105	140	
DC Blocking Voltage	V_R	20	30	40	50	60	70	80	90	100	150	200	
Average Rectified Current	I_{FAV}	2											A
Peak Forward Surge Current @=8.3ms	I_{FSM}	60											
Forward voltage	V_F	0.55			0.7		0.85					0.95	V
Reverse voltage leakage current Ta = 25℃	I_R	0.5									0.2		mA
Ta = 100℃		10					5				2		
Junction capacitance (Note.1)	C_j	220			80								pF
Thermal Resistance Junction to Ambient (Note.2)	$R_{\theta JA}$	50											℃/W
Junction Temperature	T_J	-65 to 125					-65 to 150						℃
Storage Temperature range	T_{stg}	-65 to 150											

Note.1: Measured at 1MHz and applied reverse voltage of 4.0V D.C.

Note.2: Thermal resistance from junction to ambient at 0.375”(9.5mm)lead length,P.C.B. mounted

■ Marking

NO.	SB220	SB230	SB240	SB250	SB260	SB270	SB280	SB290	SB2100	SB2150	SB2200
Marking	SB220	SB230	SB240	SB250	SB260	SB270	SB280	SB290	SB2100	SB2150	SB2200

Schottky Diodes

SB220 ~ SB2200

■ Typical Characterisitics

FIG. 1- FORWARD CURRENT DERATING CURVE

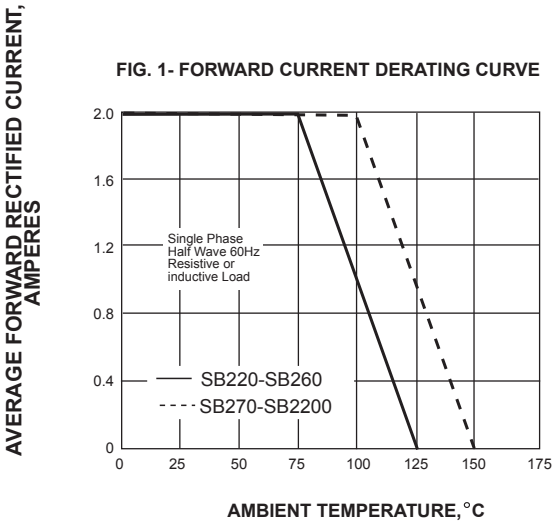


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

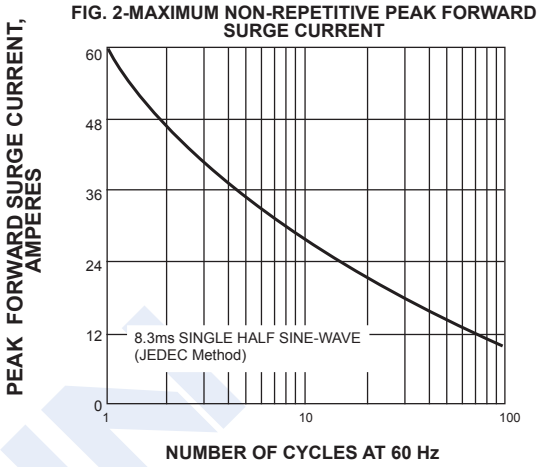


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

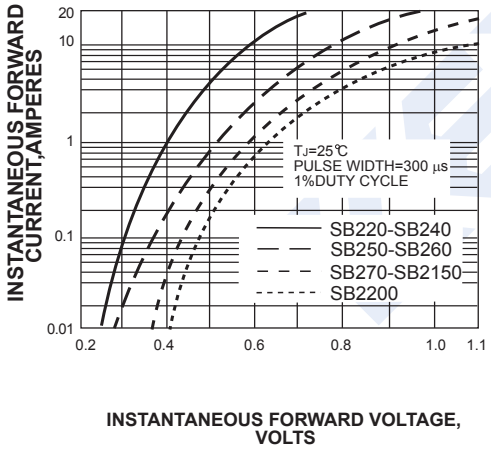


FIG. 4-TYPICAL REVERSE CHARACTERISTICS

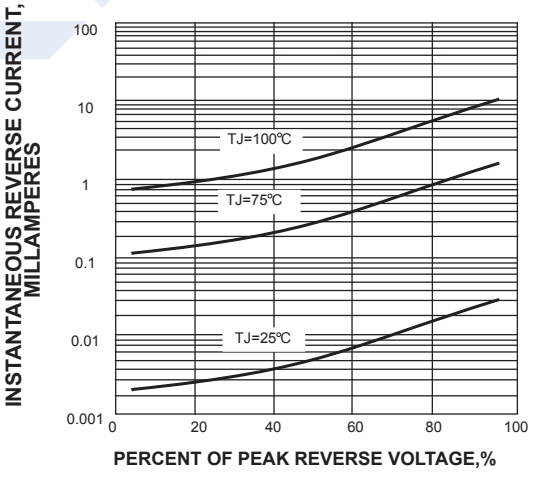


FIG. 5-TYPICAL JUNCTION CAPACITANCE

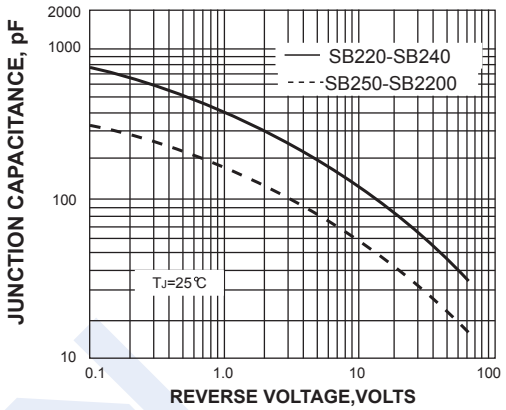


FIG. 6-TYPICAL TRANSIENT THERMAL IMPEDANCE